



BUK9222-55A

N-channel TrenchMOS logic level FET

Rev. 02 — 1 February 2011

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25 \text{ }^\circ\text{C}; T_j \leq 175 \text{ }^\circ\text{C}$	-	-	55	V
I_D	drain current	$V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ }^\circ\text{C};$ see Figure 1 ; see Figure 3	-	-	48	A
P_{tot}	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$; see Figure 2	-	-	103	W



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	-	24	$\text{m}\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$	-	17	20	$\text{m}\Omega$
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}; \text{ see Figure 12; see Figure 13}$	-	19	22	$\text{m}\Omega$
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 48 \text{ A}; V_{sup} \leq 55 \text{ V}; R_{GS} = 50 \Omega; V_{GS} = 5 \text{ V}; T_{j(init)} = 25 \text{ }^\circ\text{C}; \text{ nk; unclamped}$	-	-	160	mJ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT428 (DPAK)

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
BUK9222-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

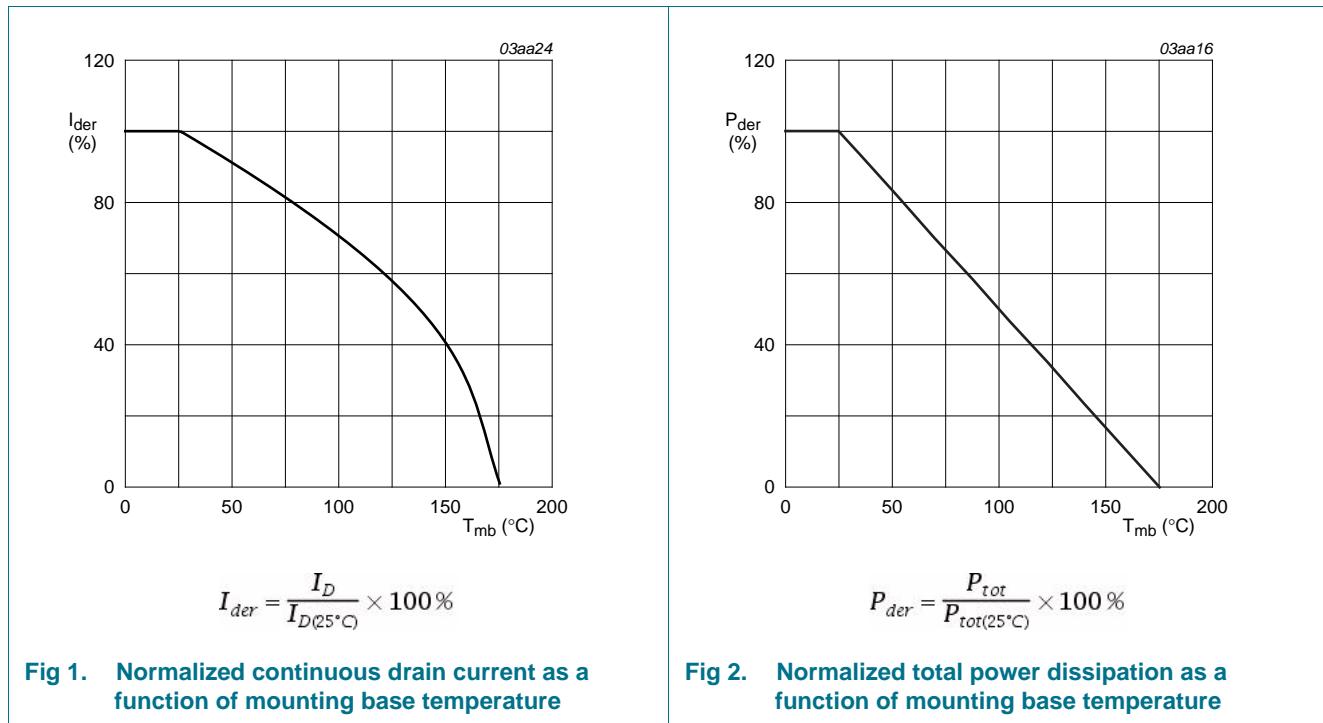
4. Limiting values

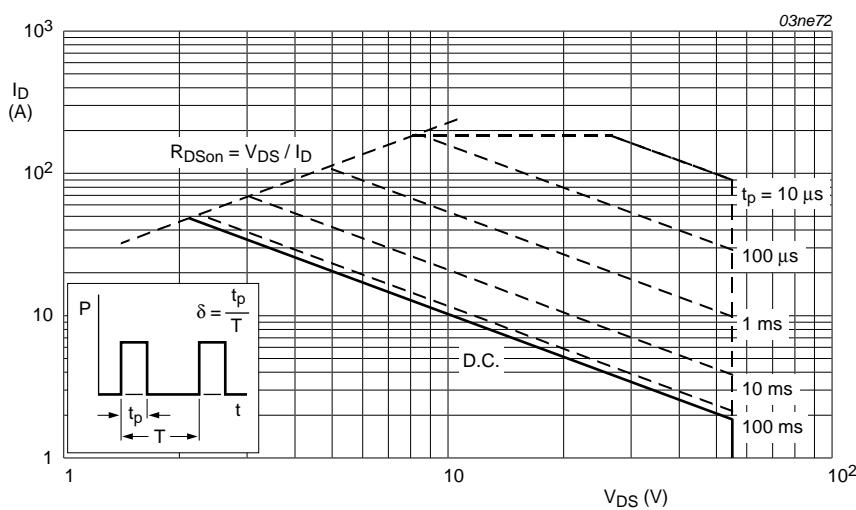
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{DS}	drain-source voltage	$T_j \geq 25^\circ\text{C}; T_j \leq 175^\circ\text{C}$	-	55	V	
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	55	V	
V_{GS}	gate-source voltage		-15	15	V	
I_D	drain current	$T_{mb} = 25^\circ\text{C}; V_{GS} = 5\text{ V}$; see Figure 1 ; see Figure 3	-	48	A	
		$T_{mb} = 100^\circ\text{C}; V_{GS} = 5\text{ V}$; see Figure 1	-	34	A	
I_{DM}	peak drain current	$T_{mb} = 25^\circ\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; see Figure 3	[1]	-	193	A
P_{tot}	total power dissipation	$T_{mb} = 25^\circ\text{C}$; see Figure 2	-	103	W	
T_{stg}	storage temperature		-55	175	°C	
T_j	junction temperature		-55	175	°C	
Source-drain diode						
I_S	source current	$T_{mb} = 25^\circ\text{C}$	-	48	A	
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25^\circ\text{C}$	-	193	A	
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 48\text{ A}$; $V_{sup} \leq 55\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}$; $T_{j(init)} = 25^\circ\text{C}$; nk; unclamped	-	160	mJ	

[1] peak drain current is limited by chip, not package.





$T_{mb} = 25^\circ C$; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	71.4	-	K/W

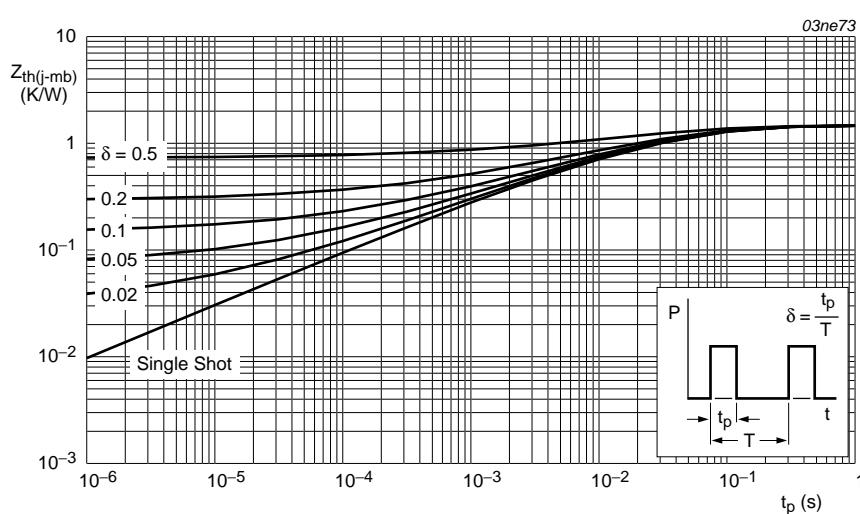
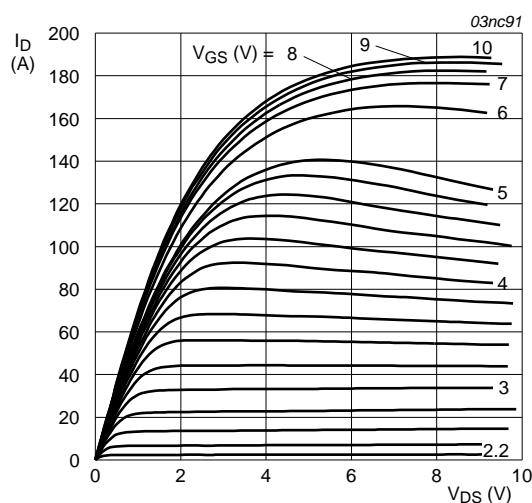


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

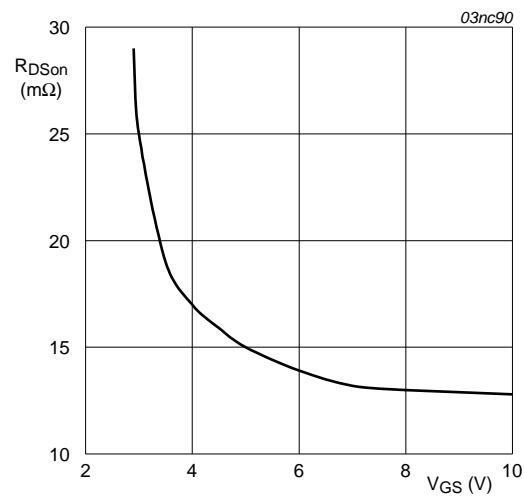
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	55	-	-	V
$V_{GS(\text{th})}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 11 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 11 $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 11	1	1.5	2	V
I_{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	0.05	10	μA
I_{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 13 $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 13	-	-	44	$\text{m}\Omega$
Dynamic characteristics						
C_{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1660	2210	pF
C_{oss}	output capacitance	$T_j = 25 \text{ }^\circ\text{C}$; see Figure 14	-	290	346	pF
C_{rss}	reverse transfer capacitance		-	194	266	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ }\Omega; V_{GS} = 5 \text{ V};$	-	19	-	ns
t_r	rise time	$R_{G(\text{ext})} = 10 \text{ }\Omega; T_j = 25 \text{ }^\circ\text{C}$	-	124	-	ns
$t_{d(off)}$	turn-off delay time		-	92	-	ns
t_f	fall time		-	93	-	ns
L_D	internal drain inductance	measured from drain to centre of die; $T_j = 25 \text{ }^\circ\text{C}$	-	2.5	-	nH
L_S	internal source inductance	measured from source lead to source bond pad; $T_j = 25 \text{ }^\circ\text{C}$	-	7.5	-	nH
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$; see Figure 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s};$ $V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	52	-	ns
Q_r	recovered charge		-	81	-	nC



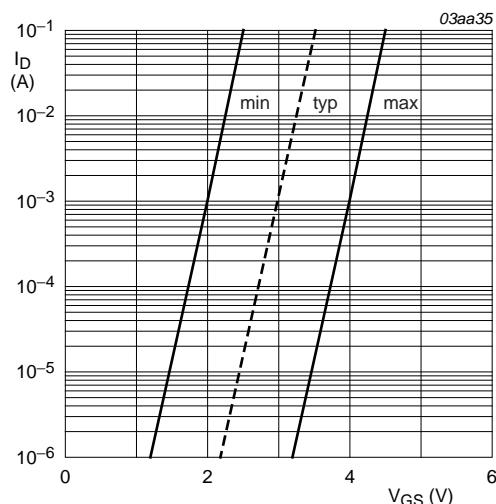
$T_j = 25^\circ C$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



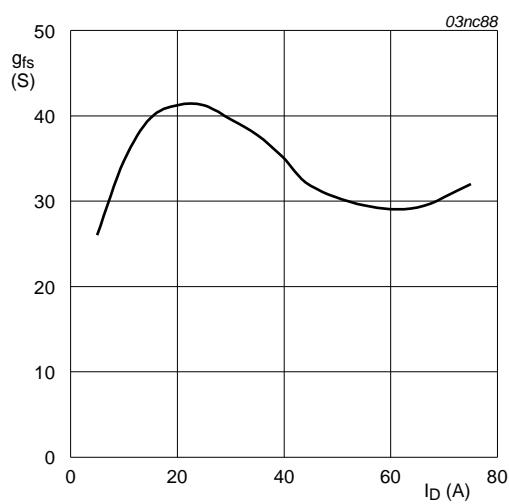
$T_j = 25^\circ C; I_D = 25A$

Fig 6. Drain-source on-state resistance as a function of drain current; typical values



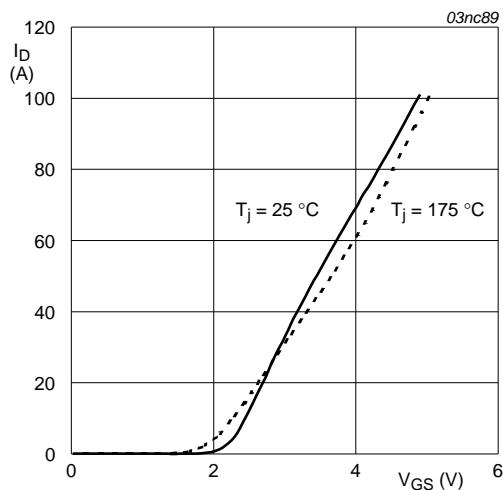
$T_j = 25^\circ C; V_{DS} = 5V$

Fig 7. Sub-threshold drain current as a function of gate-source voltage



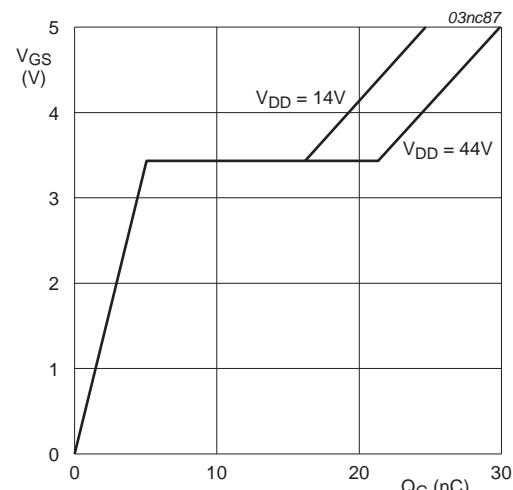
$T_j = 25^\circ C; V_{DS} = 25V$

Fig 8. Forward transconductance as a function of drain current; typical values



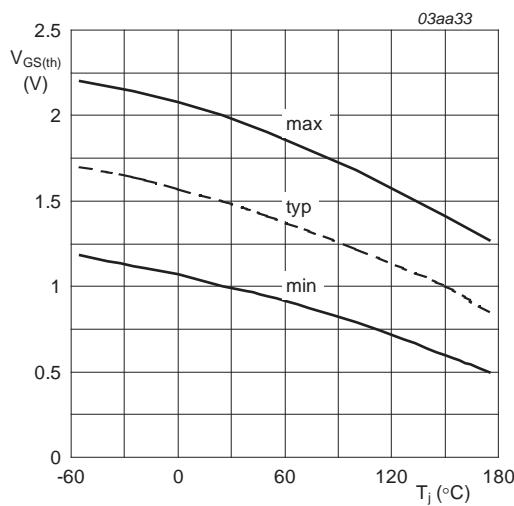
$V_{DS} = 25V$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



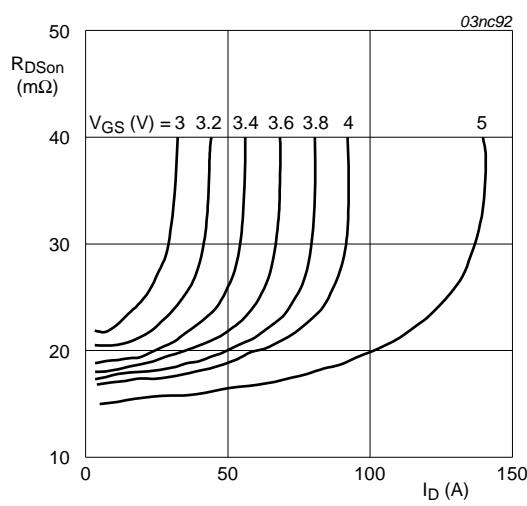
$T_j = 25^{\circ}C; I_D = 25A$

Fig 10. Gate-source voltage as a function of gate charge; typical values



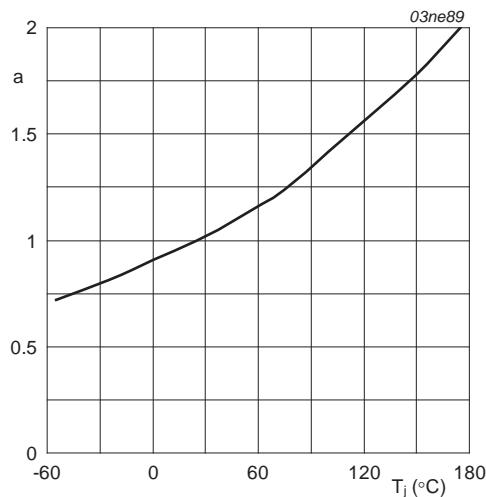
$I_D = 1mA; V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature



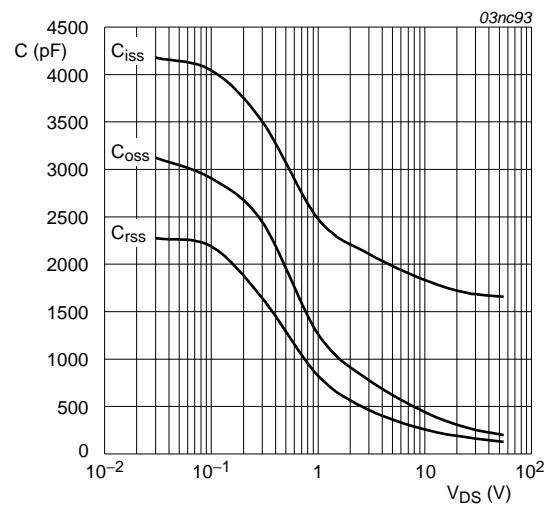
$T_j = 25^{\circ}C$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



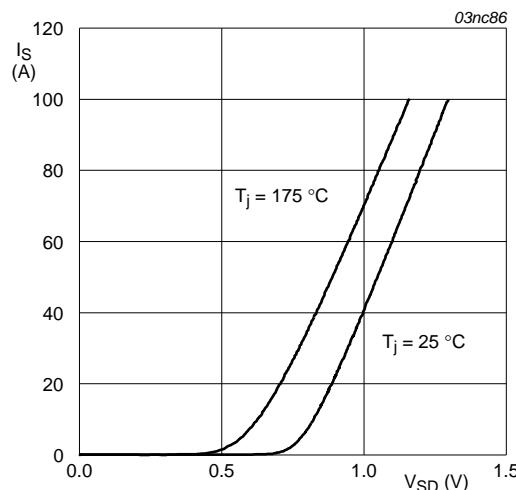
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature



$$V_{GS} = 0V; f = 1MHz$$

Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$$V_{GS} = 0V$$

Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

7. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428

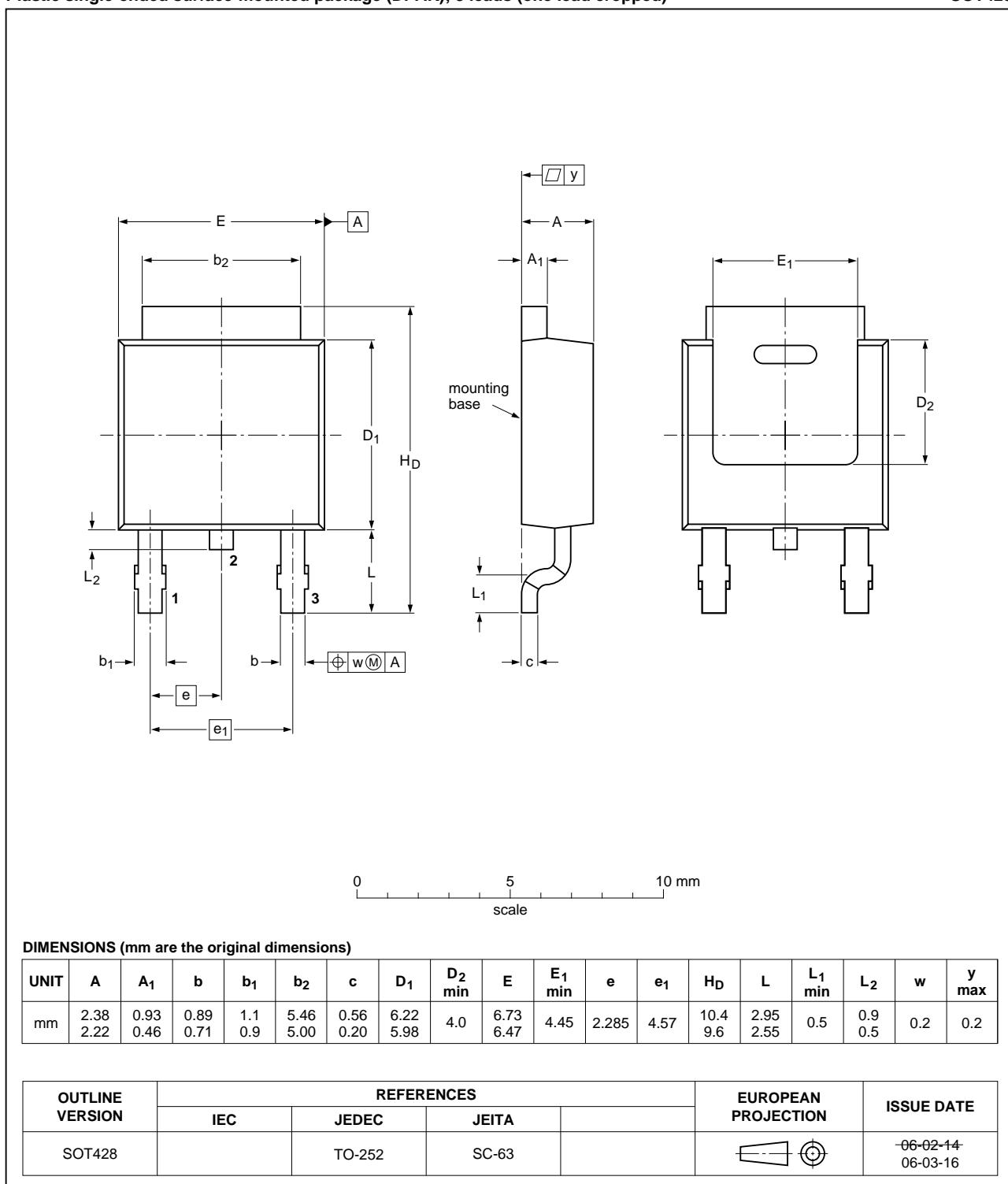


Fig 16. Package outline SOT428 (DPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9222-55A v.2	20110201	Product data sheet	-	BUK9222-55A v.1
Modifications:		<ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• Various changes to content.		
BUK9222-55A v.1	20010417	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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11. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	3
5	Thermal characteristics	4
6	Characteristics	5
7	Package outline	9
8	Revision history	10
9	Legal information	11
9.1	Data sheet status	11
9.2	Definitions	11
9.3	Disclaimers	11
9.4	Trademarks	12
10	Contact information	12

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